

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/612414	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:34
L7	13495	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:43
L8	8431	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and (tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:43
L9	6641	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and ((tft or (thin near film near transistor)) same ((semiconductor or active) near (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:44
L10	5814	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and ((tft or (thin near film near transistor)) same ((semiconductor or active) near (layer or film)) same (gate near (insulating or insulation or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:44
L11	5076	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and ((tft or (thin near film near transistor)) same ((semiconductor or active) near (layer or film)) same (gate near (insulating or insulation or dielectric)) same pixel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:45

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L12	4518	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and (((first or second or third or upper or lower or top or bottom) near (tft or (thin near film near transistor))) same ((semiconductor or active) near (layer or film)) same (gate near (insulating or insulation or dielectric)) same pixel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:46
L13	4502	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and (((first or second or third or upper or lower or top or bottom) near (tft or (thin near film near transistor))) same ((semiconductor or active) near (layer or film)) same (gate near (insulating or insulation or dielectric)) same pixel same (impurity or diffusion or source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:46
L14	4486	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and (((first or second or third or upper or lower or top or bottom) near (tft or (thin near film near transistor))) same ((semiconductor or active) near (layer or film)) same (gate near (insulating or insulation or dielectric)) same pixel same (impurity or diffusion or source or drain or source/drain) same channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:47

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L15	4479	257/72.ccls. or 257/57.ccls. or 257/59.ccls. or (257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and (((first or second or third or upper or lower or top or bottom) near (tft or (thin near film near transistor))) same ((semiconductor or active) near (layer or film)) same (((first or second or upper or lower or top or bottom) near gate near (insulating or insulation or dielectric))) same pixel same (impurity or diffusion or source or drain or source/drain) same channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:48
L16	6	(257/72.ccls. or 257/57.ccls. or 257/59.ccls. or 257/66.ccls. or 257/350.ccls. or 257/351.ccls. or 257/347.ccls. or 257/408.ccls. or 349/42.ccls. or 349/43.ccls. or 349/47.ccls.) and (((first or second or third or upper or lower or top or bottom) near (tft or (thin near film near transistor))) same ((semiconductor or active) near (layer or film)) same (((first or second or upper or lower or top or bottom) near gate near (insulating or insulation or dielectric))) same pixel same (impurity or diffusion or source or drain or source/drain) same channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/09 19:48